



STW18NK80Z

N-channel 800V - 0.34Ω - 19A - TO-247
Zener-protected SuperMESH™ Power MOSFET

General features

Type	V _{DSS}	R _{DS(on)}	I _D	P _w
STW18NK80Z	800V	<0.38Ω	19A	350W

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability

Description

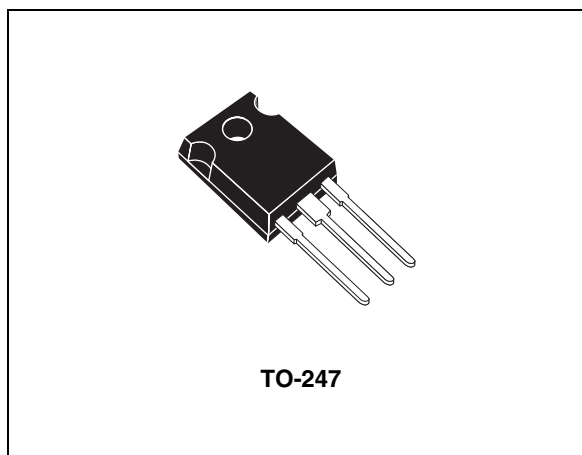
The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

Applications

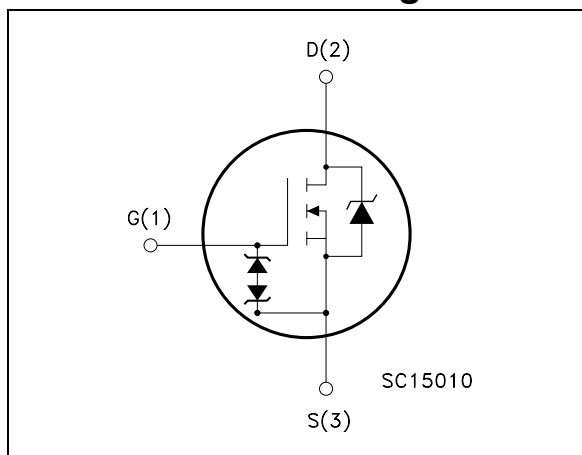
- Switching application

Order codes

Part number	Marking	Package	Packaging
STW18NK80Z	W18NK80Z	TO-247	Tube



Internal schematic diagram



Contents

1	Electrical ratings	3
	1.1 Protection features of gate-to-source zener diodes	4
2	Electrical characteristics	5
	2.1 Electrical characteristics (curves)	7
3	Test circuit	9
4	Package mechanical data	11
5	Revision history	13

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	800	V
V_{GS}	Gate- source voltage	± 30	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	19	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	12	A
$I_{DM}^{(1)}$	Drain current (pulsed)	76	A
P_{tot}	Total dissipation at $T_C = 25^\circ\text{C}$	350	W
	Derating Factor	2.4	W/ $^\circ\text{C}$
$V_{ESD(G-S)}$	Gate source ESD(HBM-C=100pF, R=1.5K Ω)	6000	V
$dv/dt^{(2)}$	Peak diode recovery voltage slope	4.5	V/ns
T_{stg}	Storage temperature	-55 to 150	$^\circ\text{C}$
T_j	Max. operating junction temperature		

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 19\text{A}$, $di/dt \leq 300\text{A}/\mu\text{s}$, $V_{DD} \leq V_{DD} < 800\text{V}$, $T_j \leq T_{JMAX}$

Table 2. Thermal data

$R_{thj-case}$	Thermal resistance junction-case max	0.36	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	50	$^\circ\text{C}/\text{W}$
T_J	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

Table 3. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	19	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{V}$)	700	mJ

Table 4. Gate-source zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-source breakdown voltage	$I_{gs} = \pm 1\text{mA}$ (open drain)	30			V

1.1 Protection features of gate-to-source zener diodes

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1mA, V_{GS} = 0$	800			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{max rating}$ $V_{DS} = \text{max rating},$ $T_C = 125^{\circ}C$			1 50	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20V$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 150\mu A$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 10A$		0.34	0.38	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15V, I_D = 10A$		19		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1MHz,$ $V_{GS} = 0$		6100 500 100		pF pF pF
$C_{oss\ eq}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0V, V_{DS} = 0V$ to 640V		240		pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 400V, I_D = 9A$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see Figure 13)		46 32 140 32		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 640V, I_D = 18A,$ $V_{GS} = 10V$ (see Figure 14)		192 34 102	250	nC nC nC

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

2. $C_{oss\ eq}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				19 76	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 19A, V_{GS} = 0$			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 18A, di/dt = 100A/\mu s,$ $V_{DD} = 40V, T_j = 25^\circ C$ (see Figure 15)		920 11 24		ns μC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 18A, di/dt = 100A/\mu s,$ $V_{DD} = 40V, T_j = 150^\circ C$ (see Figure 15)		1160 15 25.8		ns μC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

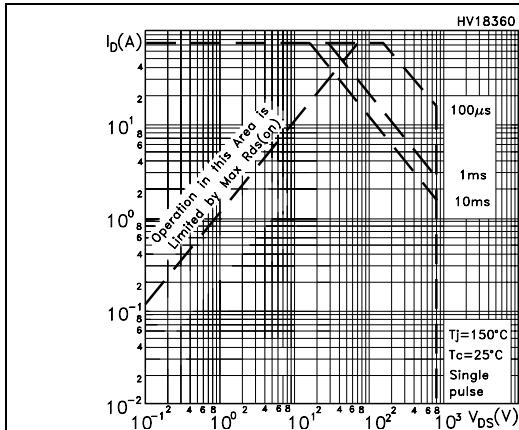


Figure 2. Thermal impedance

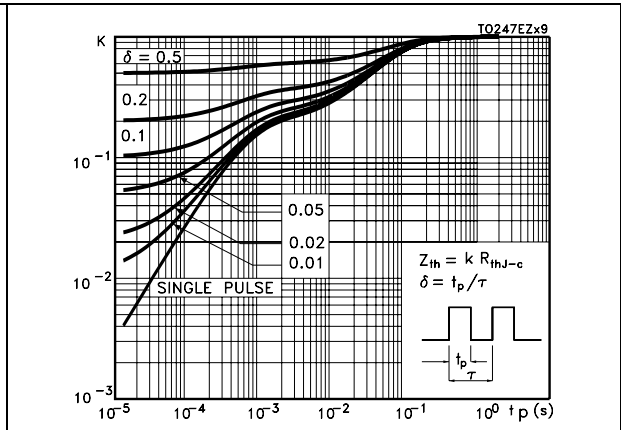


Figure 3. Output characteristics

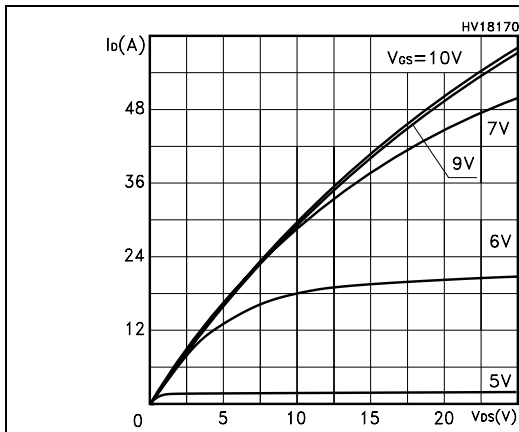


Figure 4. Transfer characteristics

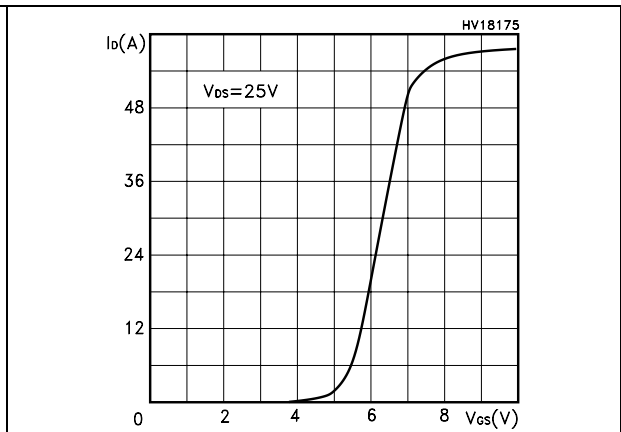


Figure 5. Transconductance

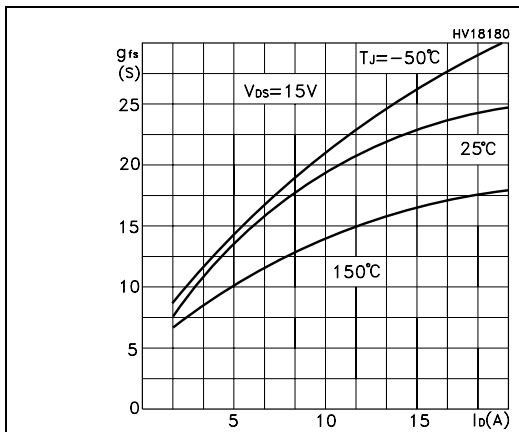


Figure 6. Static drain-source on resistance

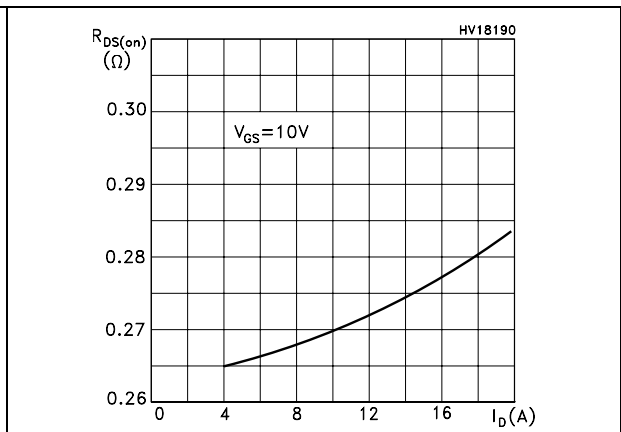


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

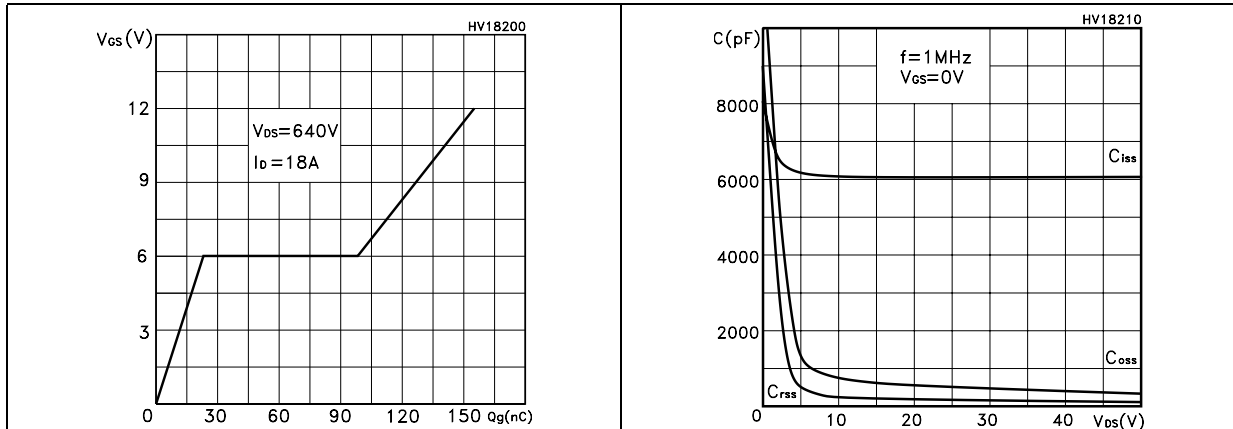


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

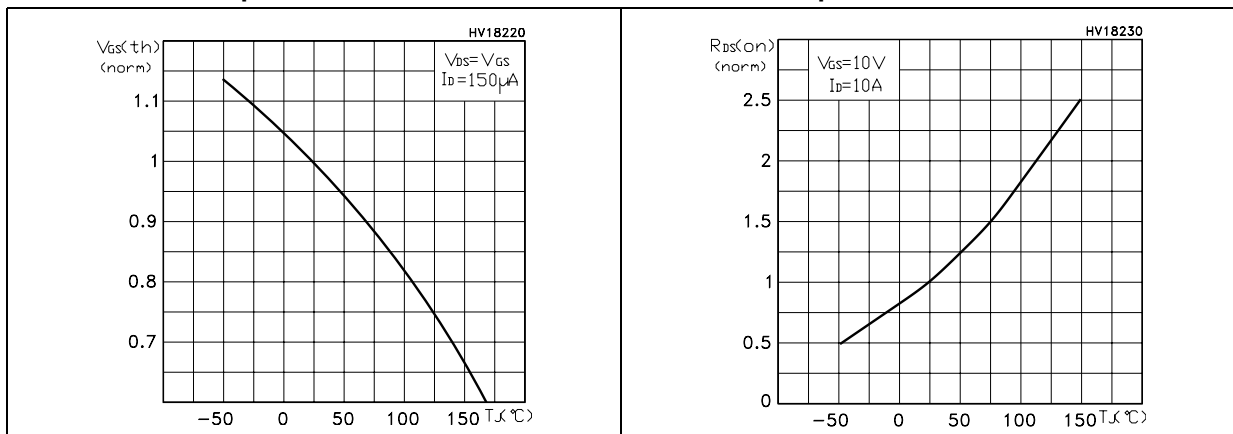
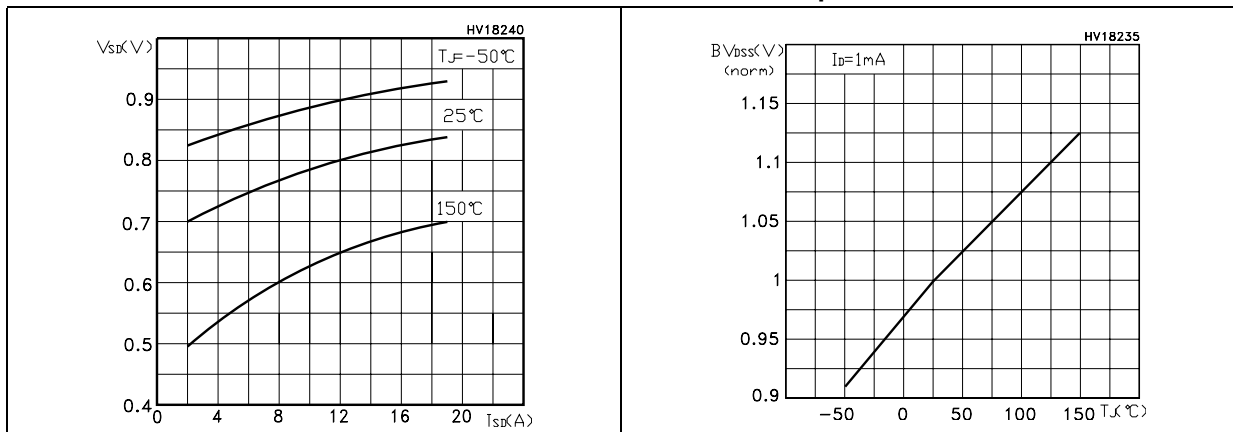


Figure 11. Source-drain diode forward characteristics Figure 12. Normalized breakdown voltage vs temperature



3 Test circuit

Figure 13. Switching times test circuit for resistive load

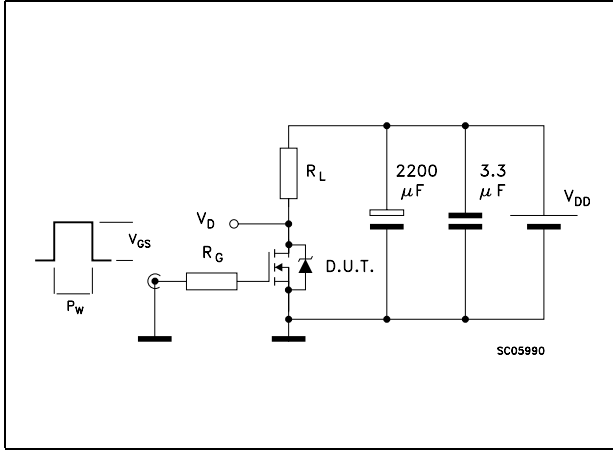


Figure 14. Gate charge test circuit

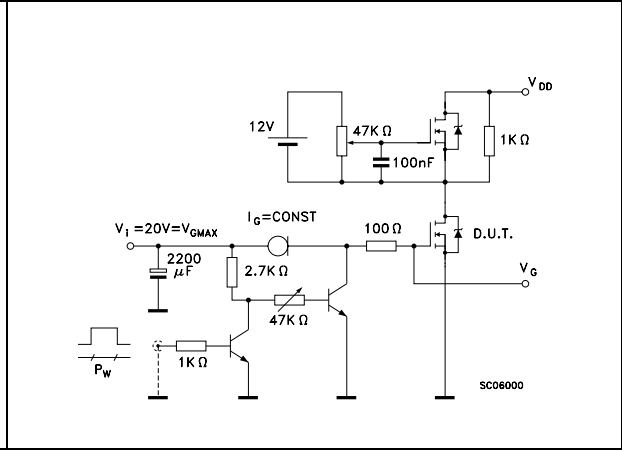


Figure 15. Test circuit for inductive load switching and diode recovery times

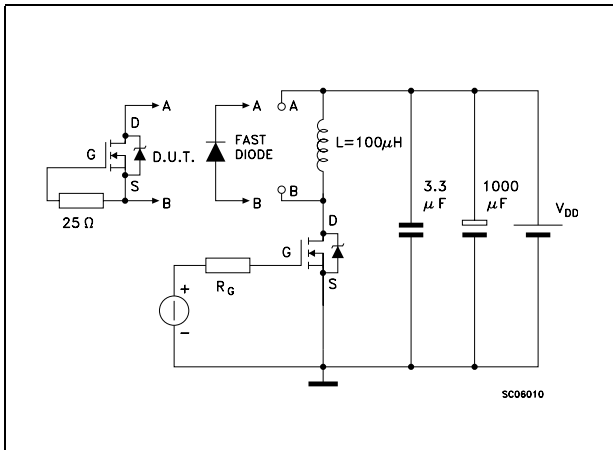


Figure 16. Unclamped Inductive load test circuit

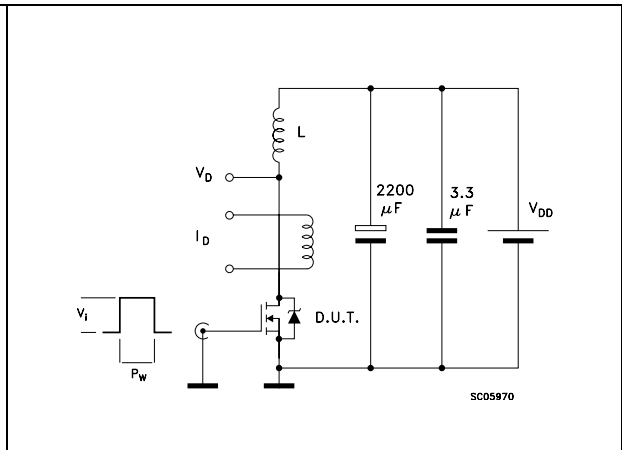
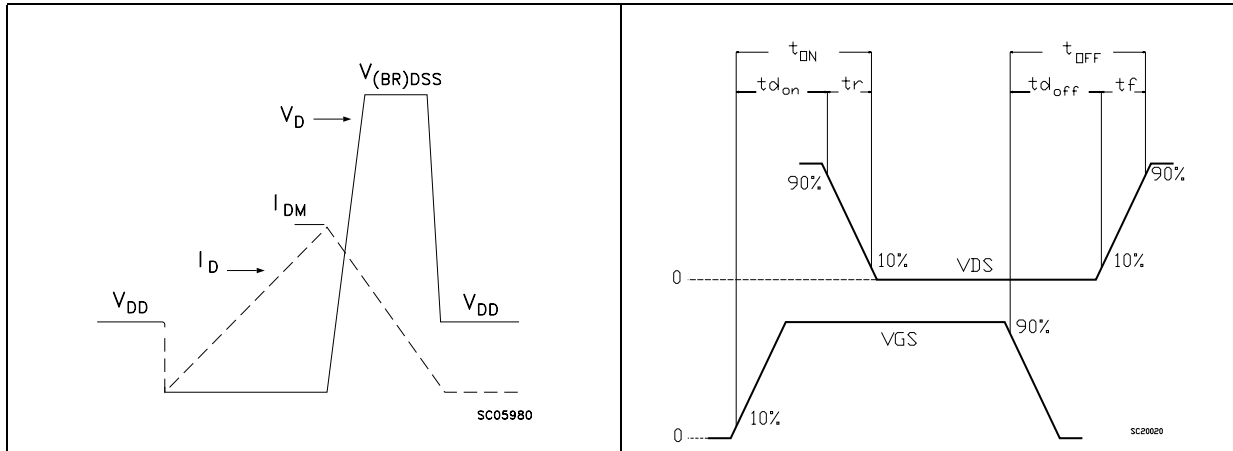


Figure 17. Unclamped inductive waveform

Figure 18. Switching time waveform

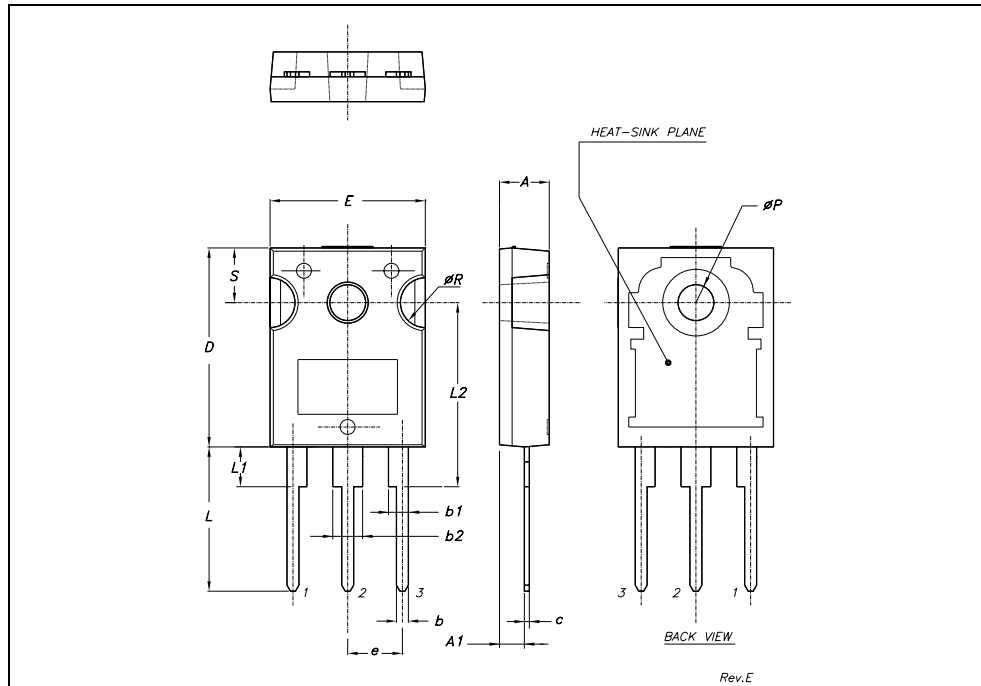


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



5 Revision history

Table 8. Revision history

Date	Revision	Changes
21-Jun-2004	3	Complete document
17-Oct-2006	4	New template, no content change

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2006 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com